

FDP5690/FDB5690

60V N-Channel PowerTrench™ MOSFET

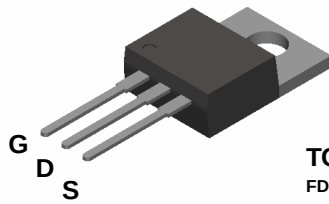
General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers.

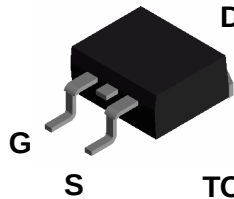
These MOSFETs feature faster switching and lower gate charge than other MOSFETs with comparable $R_{DS(on)}$ specifications resulting in DC/DC power supply designs with higher overall efficiency.

Features

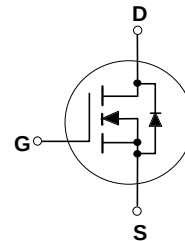
- 32 A, 60 V. $R_{DS(on)} = 0.027 \Omega @ V_{GS} = 10 \text{ V}$
 $R_{DS(on)} = 0.032 \Omega @ V_{GS} = 6 \text{ V}$.
- Critical DC electrical parameters specified at elevated temperature.
- Rugged internal source-drain diode can eliminate the need for an external Zener diode transient suppressor.
- High performance trench technology for extremely low $R_{DS(on)}$.
- 175°C maximum junction temperature rating.



TO-220
FDP Series



TO-263AB
FDB Series



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FDP5690	FDB5690	Units
V_{DSS}	Drain-Source Voltage	60		V
V_{GSS}	Gate-Source Voltage	± 20		V
I_D	Maximum Drain Current - Continuous	32		A
	- Pulsed	100		
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	58		W
	Derate above 25°C	0.4		W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-65 to +175		$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	2.6	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	$^\circ\text{C/W}$

Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape Width	Quantity
FDB5690	FDB5690	13"	24mm	800
FDP5690	FDP5690	Tube	N/A	45

Electrical Characteristics $T_c = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Drain-Source Avalanche Ratings (Note1)

W_{DSS}	Single Pulse Drain-Source Avalanche Energy	$V_{DD} = 30\text{ V}, I_D = 32\text{ A}$			80	mJ
I_{AR}	Maximum Drain-Source Avalanche Current				32	A

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	60			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C		61		mV/ $^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 48\text{ V}, V_{GS} = 0\text{ V}$			1	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 20\text{ V}, V_{DS} = 0\text{ V}$			100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -20\text{ V}, V_{DS} = 0\text{ V}$			-100	nA

On Characteristics (Note 1)

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	2.4	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, Referenced to 25°C		-6.4		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 16\text{ A},$ $V_{GS} = 10\text{ V}, I_D = 16\text{ A}, T_J = 125^\circ\text{C}$ $V_{GS} = 6\text{ V}, I_D = 15\text{ A}$		0.021 0.042 0.024	0.027 0.055 0.032	Ω
$I_{D(on)}$	On-State Drain Current	$V_{GS} = 10\text{ V}, V_{DS} = 5\text{ V}$	50			A
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}, I_D = 16\text{ A}$		32		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		1120		pF
C_{oss}	Output Capacitance			160		pF
C_{rss}	Reverse Transfer Capacitance			80		pF

Switching Characteristics (Note 1)

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 30\text{ V}, I_D = 1\text{ A},$ $V_{GS} = 10\text{ V}, R_{GEN} = 6\text{ }\Omega$		10	18	ns
t_r	Turn-On Rise Time			9	18	ns
$t_{d(off)}$	Turn-Off Delay Time			24	39	ns
t_f	Turn-Off Fall Time			10	18	ns
Q_g	Total Gate Charge	$V_{DS} = 15\text{ V},$ $I_D = 16\text{ A}, V_{GS} = 10\text{ V}$		23	33	nC
Q_{gs}	Gate-Source Charge			3.9		nC
Q_{gd}	Gate-Drain Charge			6.8		nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	(Note 1)			32	A
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 16\text{ A}$	(Note 1)	0.92	1.2	V

Note:1. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$

Typical Characteristics

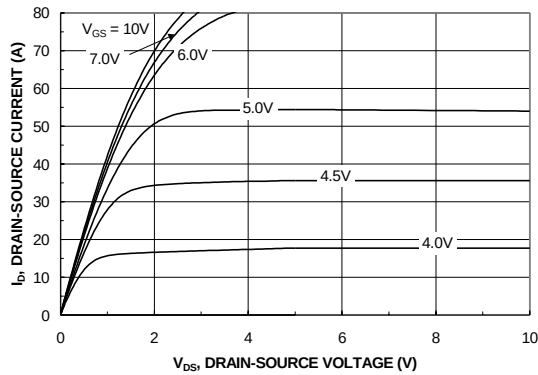


Figure 1. On-Region Characteristics.

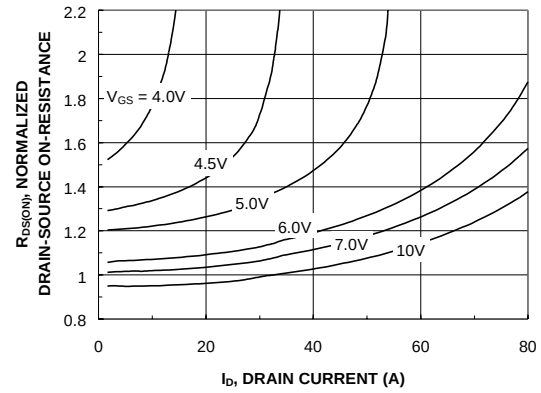


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

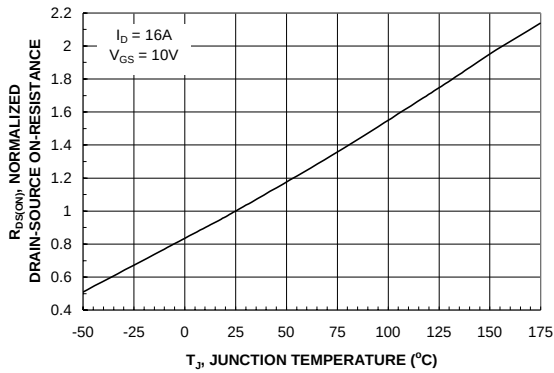


Figure 3. On-Resistance Variation with Temperature.

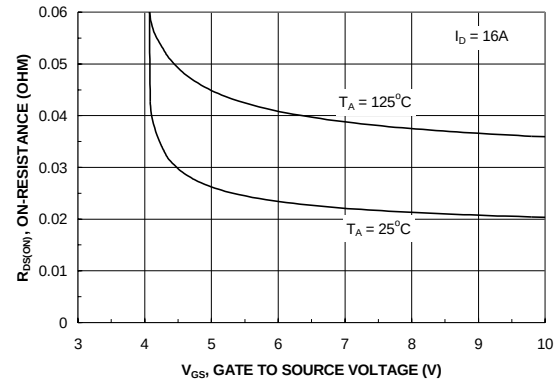


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

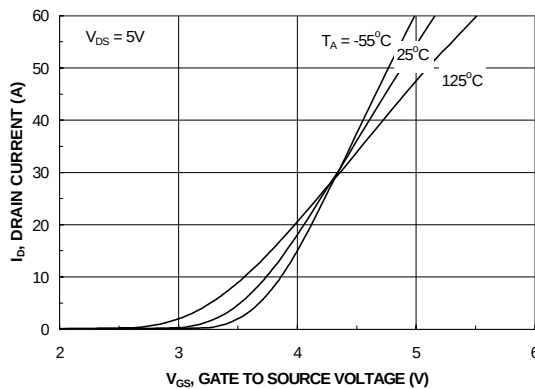


Figure 5. Transfer Characteristics.

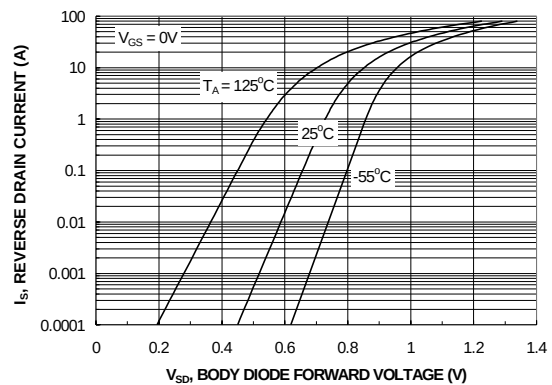


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Characteristics (continued)

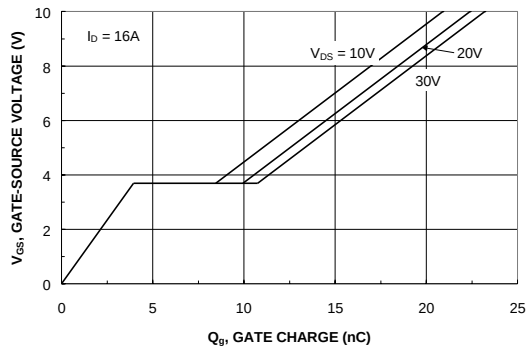


Figure 7. Gate-Charge Characteristics.

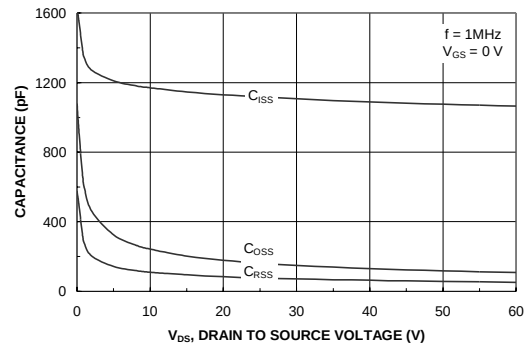


Figure 8. Capacitance Characteristics.

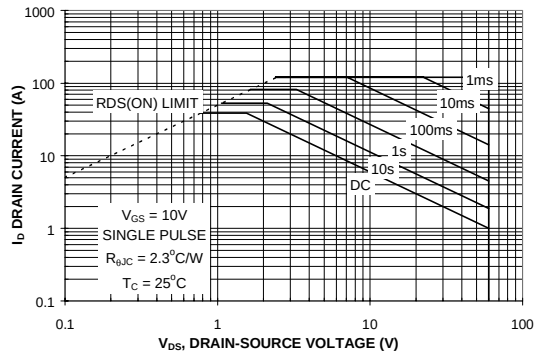


Figure 9. Maximum Safe Operating Area.

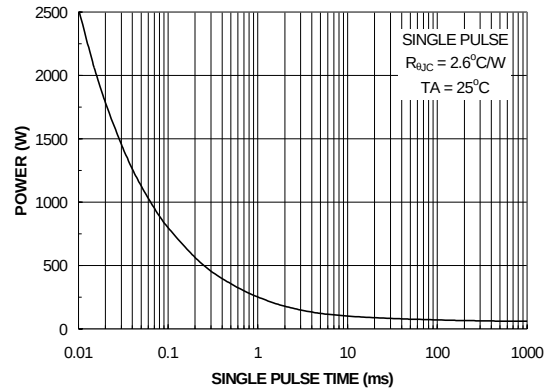


Figure 10. Single Pulse Maximum Power Dissipation.

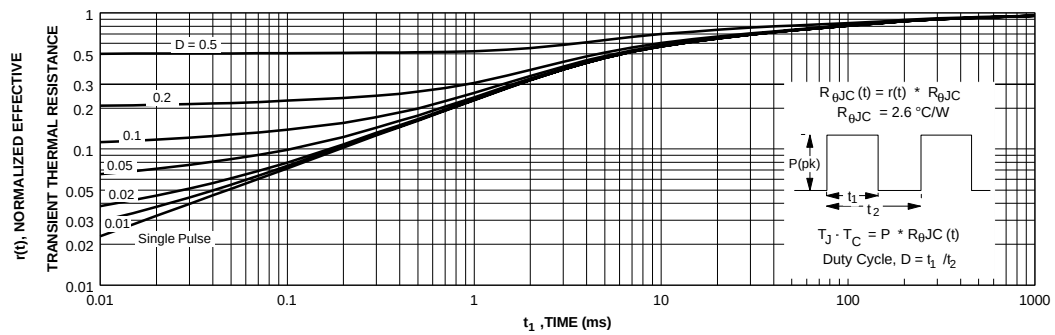


Figure 11. Transient Thermal Response Curve.

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